

PRODUCT/PROCESS CHANGE NOTIFICATION

PCN IPG-IPC/14/8322 Dated 10 Feb 2014

Qualification of a new HD lead frame and new resin

SUMITOMO G630AY for SO 8 package in ST Bouskoura (Morocco)

Table 1. Change Implementation Schedule

Forecasted implementation date for change	01-Mar-2014
Forecasted availability date of samples for customer	01-Mar-2014
Forecasted date for STMicroelectronics change Qualification Plan results availability	03-Feb-2014
Estimated date of changed product first shipment	12-May-2014

Table 2. Change Identification

Product Identification (Product Family/Commercial Product)	See attached
Type of change	Package assembly material change
Reason for change	Capacity increase
Description of the change	Introduction of a new HD lead frame and new resin SIMITOMO G630AY for the assembly of products housed in SO 08 package, in ST Bouskoura (Morocco).
Change Product Identification	By date code and relevant traceability
Manufacturing Location(s)	

Table 3. List of Attachments

Customer Part numbers list	
Qualification Plan results	

Customer Acknowledgement of Receipt	PCN IPG-IPC/14/8322
Please sign and return to STMicroelectronics Sales Office	Dated 10 Feb 2014
Qualification Plan Denied	Name:
Qualification Plan Approved	Title:
	Company:
🗖 Change Denied	Date:
Change Approved	Signature:
Remark	

Name	Function
Sandrini, Francesca Marta	Marketing Manager
Vavassori, Emanuele	Marketing Manager
Sandrini, Francesca Marta	Product Manager
Vavassori, Emanuele	Product Manager
Moretti, Paolo	Q.A. Manager
Motta, Antonino	Q.A. Manager

DOCUMENT APPROVAL



WHAT:

We have qualified a new HD lead frame for the assembly of products housed in SO 08 package in ST Bouskoura (Morocco). In addition we have introduced a new halogen free resin SUMITOMO G630AY to replace the current SUMITOMO G700K.

WHY:

To rationalize manufacturing and to increase our production capacity.

HOW:

As per the attached Reliability Qualification plan, we have evaluated and qualified the a.m. new material through trials performed on 3 test vehicles (UE27BD6, 0303AC6 and U093ADZ).

WHEN:

The new HD lead frame and resin will be implemented from March, 2014.

Samples of the a.m. test vehicles are available. For all the other involved products, they can be provided on request, in 4 weeks A.R.O.



Reliability Report Qualification of new HD LF and new resin SUMITOMO G630AY for SO8 package in BOUSKOURA

Genera	Information	Location	S
Product Line	UE27	Wafer fab location	ANG MO KIO 6"
Product division	I&PC		POUSKOUDA
Package	S08	Assembly plant location	(Morocco)
Silicon process technology	BCD2S	Reliability assessment	Pass
Genera	Information	Location	IS
Product Line	0303	Wafer fab location	ANG MO KIO 6"
Product division	I&PC		
Package	SO8	Assembly plant location	BOUSKOURA (Morocco)
Silicon process technology	BIPOLAR	Reliability assessment	Pass
Genera	Information	Location	S
Product Line	U093	Wafer fab location	ANG MO KIO 6"
Product division	I&PC		ROUSKOUDA
Package	S08	Assembly plant location	(Morocco)
Silicon process technology	BCD1	Reliability assessment	Pass

DOCUMENT HISTORY

Version	Date	Pages	Author	Comment
1.0	23-Jan-14	9	S. Regini	Original document

Issued by Samantha Regini Approved by Antonino Motta





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<u>1</u> APPLICABLE AND REFERENCE DOCUMENTS

Document referenceShort descriptionAEC-Q100: Stress test qualification for integrated circuits8161393: General Specification For Product Development



2 RELIABILITY EVALUATION OVERVIEW

2.1 Objectives

This report contains all the reliability activities in order to evaluate the new HD lead frame (320 units/strip vs 120 units/strip) used for the assembly of SO8 package in BOUSKOURA (Morocco) assy plant.

With respect the current pre-plated lead frame, the new HD LF is a Cu - Ag spot lead frame; a pure tin lead plating process step will be introduced in the process flow after post mold curing step and before cropping.



Fig1: Current SO8 LF (5x3x8=120 units /strip; 57.7x215.7 mm)



Fig2: New HD SO8 LF (10x2x16=320 units /strip; 70.8x248 mm)

In addiction a new resin halogen free SUMITOMO G630AY will be introduced to substitute the current SUMITOMO G700K resin.

The reliability evaluations have been performed 3 test vehicles: UE27BD6, 0303AC6 and U093ADZ devices diffused in AMK6" and assembled in SO8 package in Bouskoura.

According to Reliability Qualification Plan, below is the list of the trials performed:

Package Oriented Tests

- Preconditioning
- Temperature Cycling
- Autoclave
- High Temperature Storage Life
- Temperature Humidity Bias

2.2 Conclusion

Taking in account the results of the trials performed the new HD LF and the new resin halogen free SUMITOMO G630AY used in SO8 package assembled in BOUSKOURA (Morocco) ASSY PLANT can be qualified from reliability viewpoint.



3 DEVICE CHARACTERISTICS

3.1 Traceability

3.1.1 TV1 - UE27BD6

Wafer fab information		
Wafer fab manufacturing location	ANG MO KIO	
Wafer diameter	6"	
Wafer thickness	375 μm	
Silicon process technology	BCD2S	
Die finishing back side	CHROMIUM / NIKEL/ GOLD	
Die size	1790 *1870 μm	
Bond pad metallization layers	AlSiCu	
Passivation	SiN/POLYIMIDE	
Metal levels	2	

Assembly Information		
Assembly plant location	BOUSKOURA (Morocco)	
Package description	SO 8	
Die pad size	94 x125 mils	
Frame material	SO 8L 94x125 HD OpA 320u SpAg - Sumitomo	
Molding compound	SUMITOMO EME-G630AY	
Wires bonding materials/diameters	Cu 1 mil	
Die attach material	ABLEBOND 8601S-25	
Lead solder material	Sn	



3.1.2 TV2 - 0303AC6

Wafer fab information		
Wafer fab manufacturing location	ANG MO KIO	
Wafer diameter	6"	
Wafer thickness	375 μm	
Silicon process technology	BIPOLAR	
Die finishing back side	RAW SILICON	
Die size	1890*2120 μm	
Bond pad metallization layers	AlSiCu	
Passivation	SiN	
Metal levels	1	

Assembly Information		
Assembly plant location	BOUSKOURA (Morocco)	
Package description	SO 8	
Die pad size	94 x125 mils	
Frame material	SO 8L 94x125 HD OpA 320u SpAg / Supplier Sumitomo	
Molding compound	SUMITOMO EME-G630AY	
Wires bonding materials/diameters	Cu 1mils	
Die attach material	GLUE ABLEBOND 8601S-25	
Lead solder material	Sn	

3.1.3 TV3 - U093ADZ

Wafer fab information					
Wafer fab manufacturing location	ANG MO KIO				
Wafer diameter	6"				
Wafer thickness	375 μm				
Silicon process technology	BCD1				
Die finishing back side	CHROMIUM / NIKEL/ GOLD				
Die size	2590,2060 μm				
Bond pad metallization layers	AlSi				
Passivation	SiN				
Metal levels	1				

Assembly Information					
Assembly plant location	BOUSKOURA (Morocco)				
Package description	SO 8				
Die pad size	94 x125 mils				
Frame Material	SO 8L 94x125 HD OpA 320u SpAg / Supplier Sumitomo				
Molding compound	SUMITOMO EME-G630AY				
Wires bonding materials/diameters	Cu 1 mil				
Die attach material	ABLEBOND 8601S-25				
Lead solder material	Sn				



4 TESTS RESULTS SUMMARY

4.1 Test plan and results summary

4.1.1 TV1 - UE27BD6

Package Oriented Tests								
Test	Method	Conditions	Failure/SS			_		
			Lot 1	Lot 2	Lot 3	Duration	Note	
PC	Pre-Conditioning: Moisture sensitivity level 1							
		168h 85°C/85% - 3 reflow PBT 260°C	0/154				no delami nation	
AC	Autoclave							
	PC before	121°C 2atm	0/77			168h		
тс	Temperature Cycling							
	PC before	Temp. range: -65/+150°C	0/77			1000cy		
HTSL	High Temperature Storage							
	No bias	Tamb=150°C	0/77			1000h		

4.1.2 TV2 - 0303AC6

Package Oriented Tests								
Test	Method	Conditions		Failure/SS				
			Lot 1	Lot 2	Lot 3	Duration	Note	
PC	Pre-Conditioning: Moisture sensitivity level 1							
		168h 85°C/85% - 3 reflow PBT 260°C	0/231				No delami nation	
AC	Autoclave							
	PC before	121°C 2atm	0/77			96h		
TC	Temperature Cycling							
	PC before	Temp. range: -65/+150°C	0/77			1000cy		
HTSL	High Temperature Storage							
	No bias	Tamb=150°C	0/77			1000h		
THB	Temperature Humidity Bias							
	PC before	Ta=85°C, 85%R.H, Vcc=+25V	0/77			1000h		



4.1.3 TV3 - U093ADZ

Package Oriented Tests							
Test	Method	Conditions		Failure/SS			
			Lot 1	Lot 2	Lot 3	Duration	Note
PC	Pre-Conditioning: Moisture sensitivity level 1						
		168h 85°C/85% - 3 reflow PBT 260°C	0/154				No delami nation
AC	Autoclave						
	PC before	121°C 2atm	0/77			168h	
ТС	Temperature Cycling						
	PC before	Temp. range: -65/+150°C	0/77			1000cy	
HTSL	High Temperature Storage						
	No bias	Tamb=150°C	0/77			1000h	



5 TESTS DESCRIPTION & DETAILED RESULTS

5.1 Package oriented tests

5.1.1 Pre-Conditioning

The device is submitted to a typical temperature profile used for surface mounting, after a controlled moisture absorption.

The scope is to verify that the surface mounting stress does not impact on the subsequent reliability performance. The typical failure modes are "pop corn" effect and delamination.

5.1.2 High Temperature Storage

The device is stored in unbiased condition at the max. temperature allowed by the package materials, sometimes higher than the max. operative temperature.

The scope is to investigate the failure mechanisms activated by high temperature, typically wire-bonds solder joint ageing, data retention faults, metal stress-voiding

5.1.3 Thermal Cycles

The purpose of this test is to evaluate the thermo mechanical behavior under moderate thermal gradient stress. Test flow chart is the following:

- Initial testing @ Ta=25°C.
- Readout @ 500 cycles.
- Final Testing @ 1000 cycles @ Ta=25°C.

TEST CONDITIONS:

- Ta= -50°C to +150°C(air)
- 15 min. at temperature extremes
- 1 min. transfer time

5.1.4 Autoclave

The purpose of this test is to point out critical water entry path with consequent corrosion phenomena related to chemical contamination and package hermeticity.

- Test flow chart is the following:
 - Initial testing @ Ta=25°C.
 - Final Testing (168hrs) @ Ta=25°C.

TEST CONDITIONS:

- P=2.08 atm
- Ta=121°C
- test time= 168 hrs

5.1.5 Temperature Humidity Bias

The test is addressed to put in evidence problems of the die-package compatibility related to phenomena activated in wet conditions such as electro-chemical corrosion.

The device is stressed in static configuration approaching some field status like power down. Temperature, Humidity and Bias are applied to the device in the following environmental conditions => Ta=85°C / RH=85%. Input pins to Low / High Voltage (alternate) to maximize voltage contrast. Test Duration 1000 h.

The flow chart is the following:

- Initial testing @ Ta=25°C, 85°C
- Check @ 168 and 500hrs
- Final Testing (1000 hr.) @ Ta=25°C, 85°

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